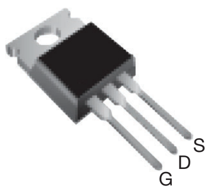
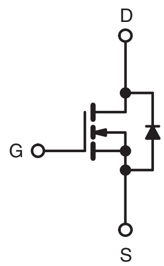
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	100	
$R_{DS(on)}$ (Ω)	V_{GS} = 5.0 V	0.077
Q_g (Max.) (nC)	64	
Q_{gs} (nC)	9.4	
Q_{gd} (nC)	27	
Configuration	Single	

TO-220AB





N-Channel MOSFET

FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at V_{GS} = 4 V and 5 V
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC

Pb Available
RoHS* COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRL540PbF
	SiHL540-E3
SnPb	IRL540
	SiHL540

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	100	V
Gate-Source Voltage			V_{GS}	± 10	
Continuous Drain Current	V_{GS} at 5.0 V	T_C = 25 °C	I_D	28	A
		T_C = 100 °C		20	
Pulsed Drain Current[a]			I_{DM}	110	
Linear Derating Factor				1.0	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	440	mJ
Avalanche Current[a]			I_{AR}	28	A
Repetitive Avalanche Energy[a]			E_{AR}	15	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	150	W
Peak Diode Recovery dV/dt[c]			dV/dt	5.5	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[d]	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

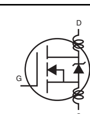
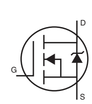
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = 25 V, starting T_J = 25 °C, L = 841 μH, R_g = 25 Ω, I_{AS} = 28 A (see fig. 12c).
c. $I_{SD} \le 28$ A, $dI/dt \le 170$ A/μs, $V_{DD} \le V_{DS}$, $T_J \le 175$ °C.
d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greasd Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		100	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA		-	0.12	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 μA		1.0	-	2.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 10 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V		-	-	25	μA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 150 °C		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 5.0 V	I_D = 17 A[b]	-	-	0.077	Ω
		V_{GS} = 4.0 V	I_D = 14 A[b]	-	-	0.11	
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 17 A		12	-	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	2200	-	pF
Output Capacitance	C_{oss}			-	560	-	
Reverse Transfer Capacitance	C_{rss}			-	140	-	
Total Gate Charge	Q_g	V_{GS} = 5.0 V	I_D = 28 A, V_{DS} = 80 V, see fig. 6 and 13[b]	-	-	64	nC
Gate-Source Charge	Q_{gs}			-	-	9.4	
Gate-Drain Charge	Q_{gd}			-	-	27	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, I_D = 28 A, R_g = 9.0 Ω, R_D = 1.7 Ω, see fig. 10[b]		-	8.5	-	ns
Rise Time	t_r			-	170	-	
Turn-Off Delay Time	$t_{d(off)}$			-	35	-	
Fall Time	t_f			-	80	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	28	A
Pulsed Diode Forward Current[a]	I_{SM}			-	-	110	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = 28 A, V_{GS} = 0 V[b]		-	-	2.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 28 A, dI/dt = 100 A/μs[b]		-	200	260	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	1.7	2.90	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

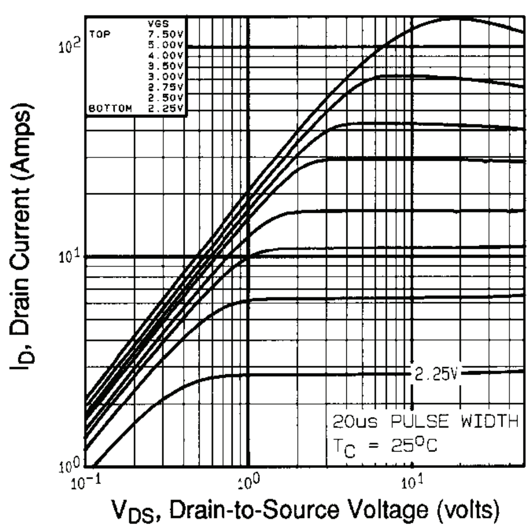


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

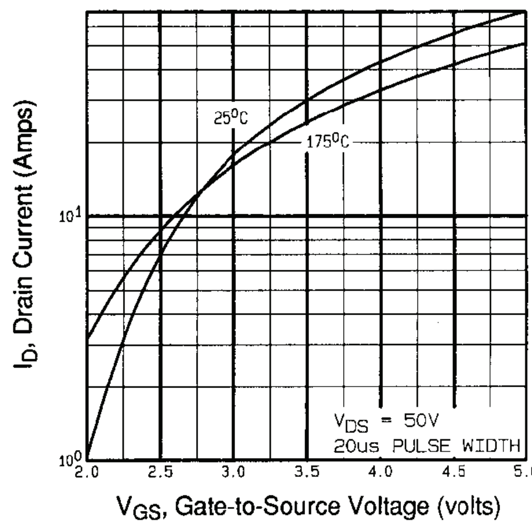


Fig. 3 - Typical Transfer Characteristics

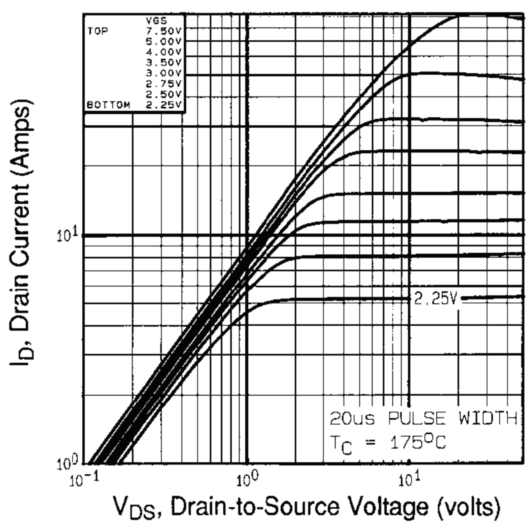


Fig. 2 - Typical Output Characteristics, T_C = 175 °C

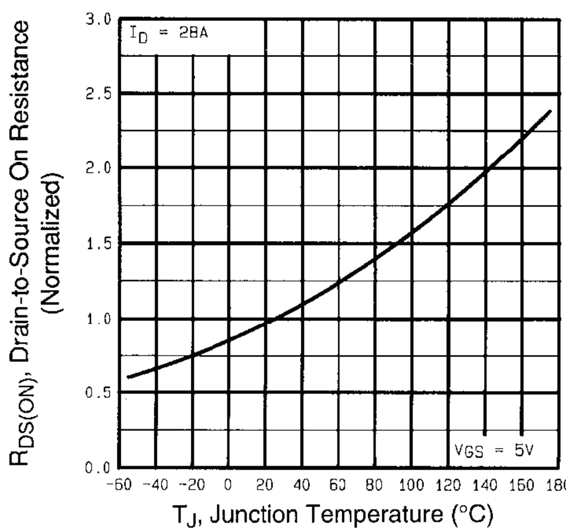


Fig. 4 - Normalized On-Resistance vs. Temperature

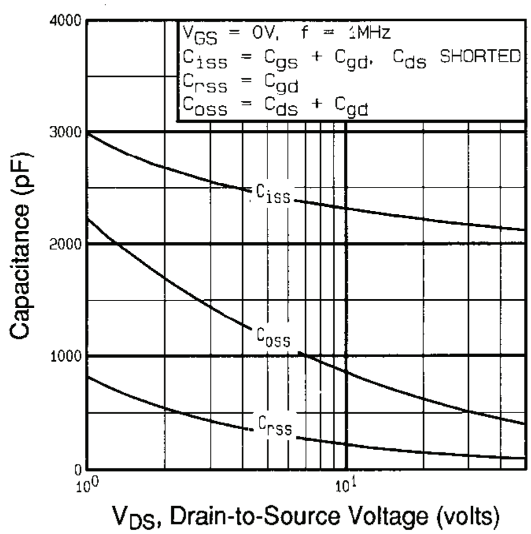


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

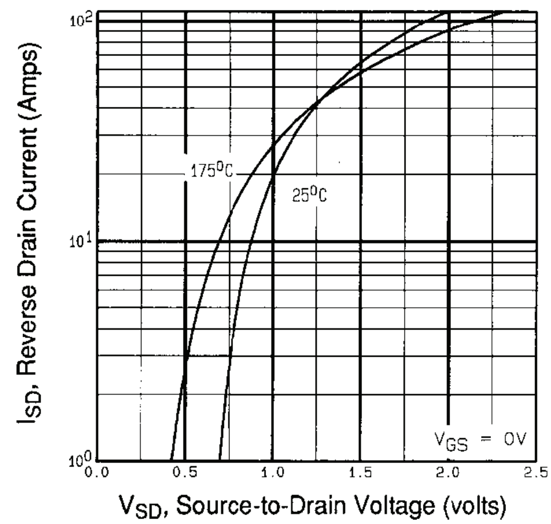


Fig. 7 - Typical Source-Drain Diode Forward Voltage

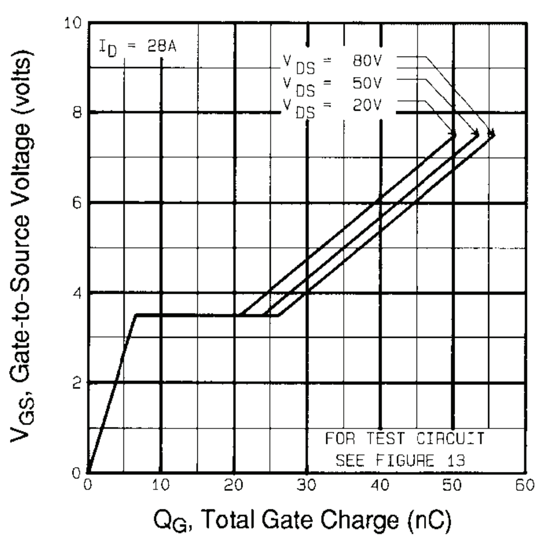


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

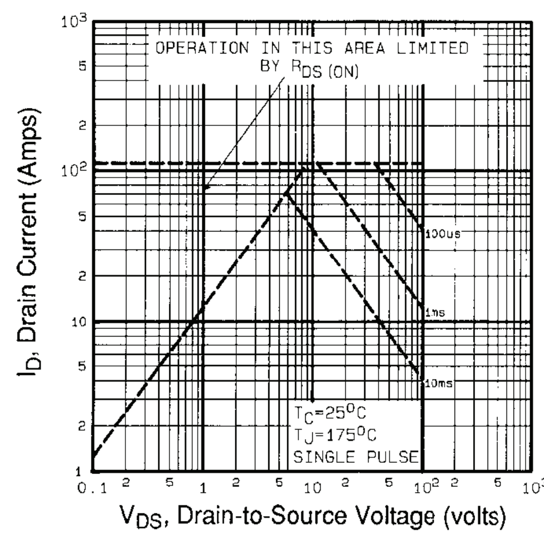


Fig. 8 - Maximum Safe Operating Area

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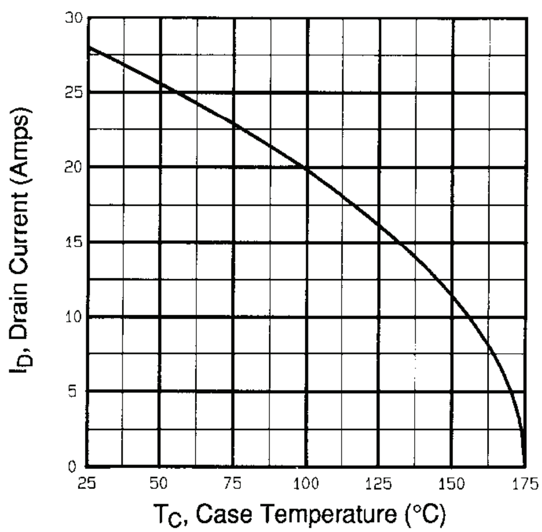


Fig. 9 - Maximum Safe Operating Area

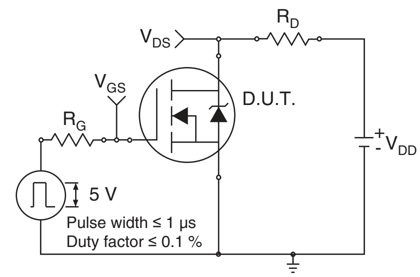


Fig. 10a - Switching Time Test Circuit

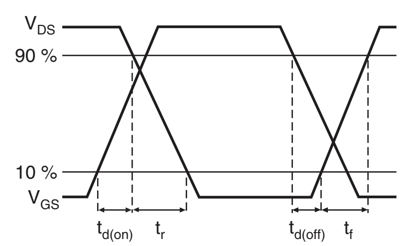


Fig. 10b - Switching Time Waveforms

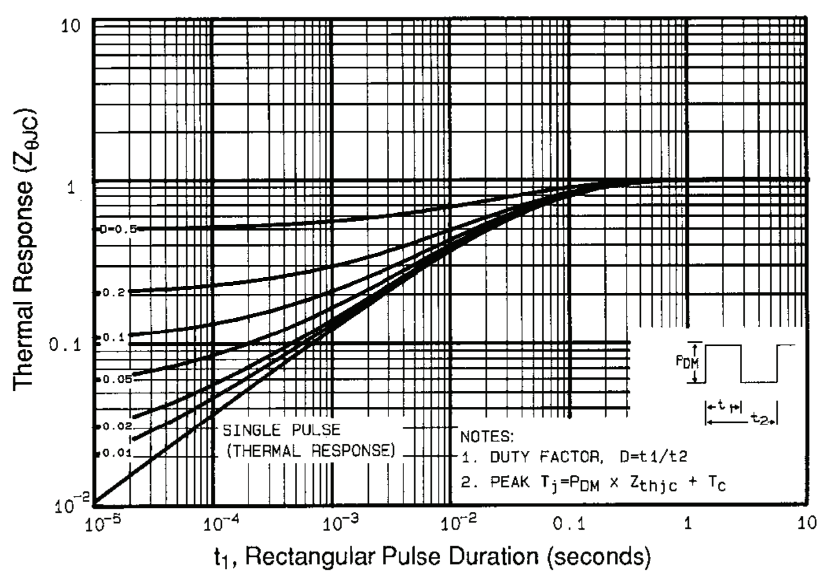


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

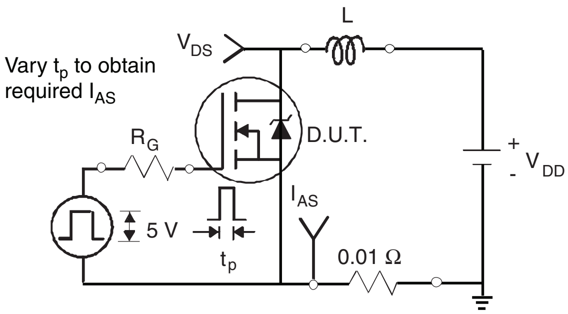


Fig. 12a - Unclamped Inductive Test Circuit

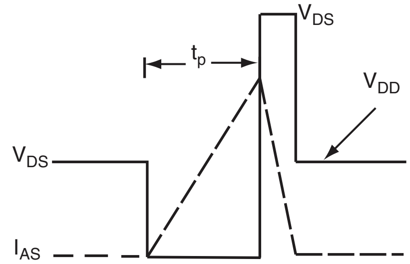


Fig. 12b - Unclamped Inductive Waveforms

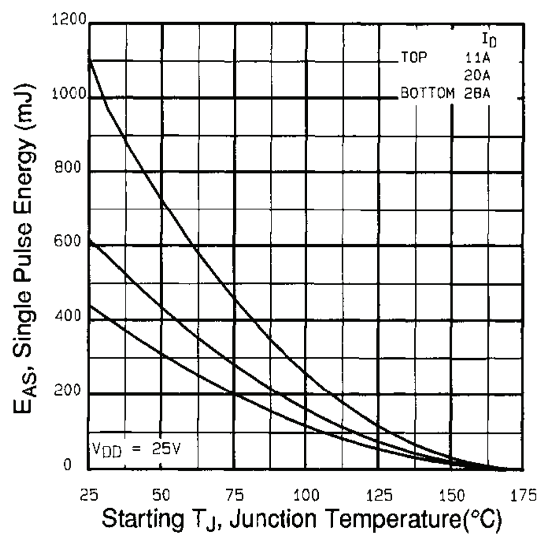


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

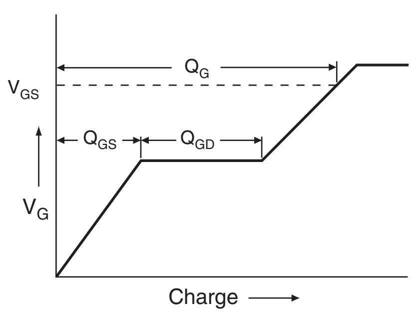


Fig. 13a - Basic Gate Charge Waveform

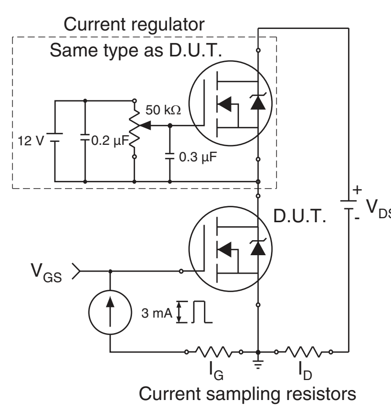
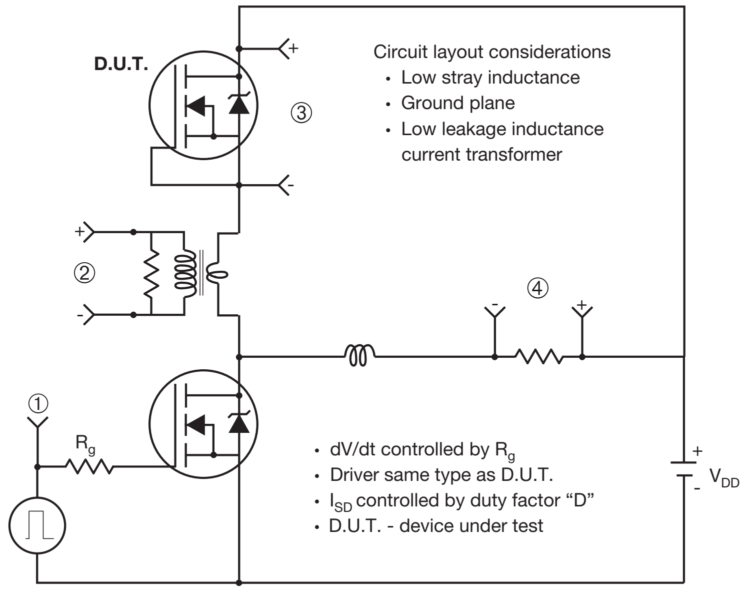
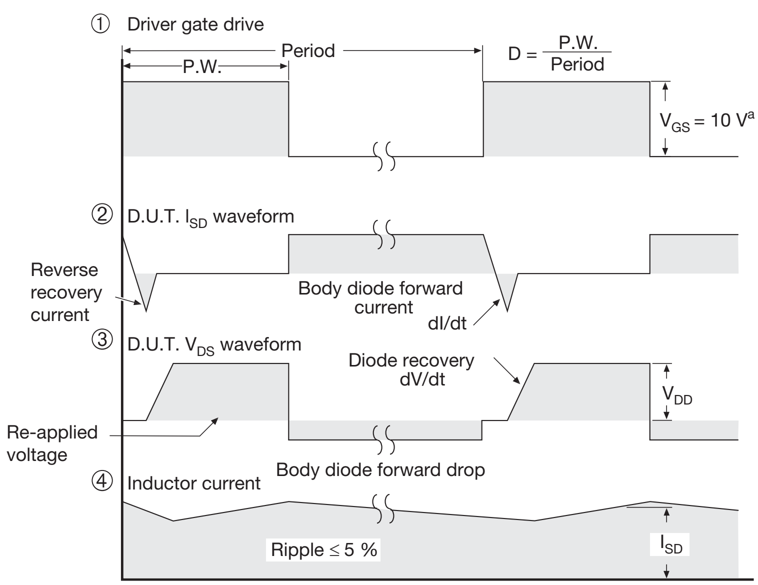


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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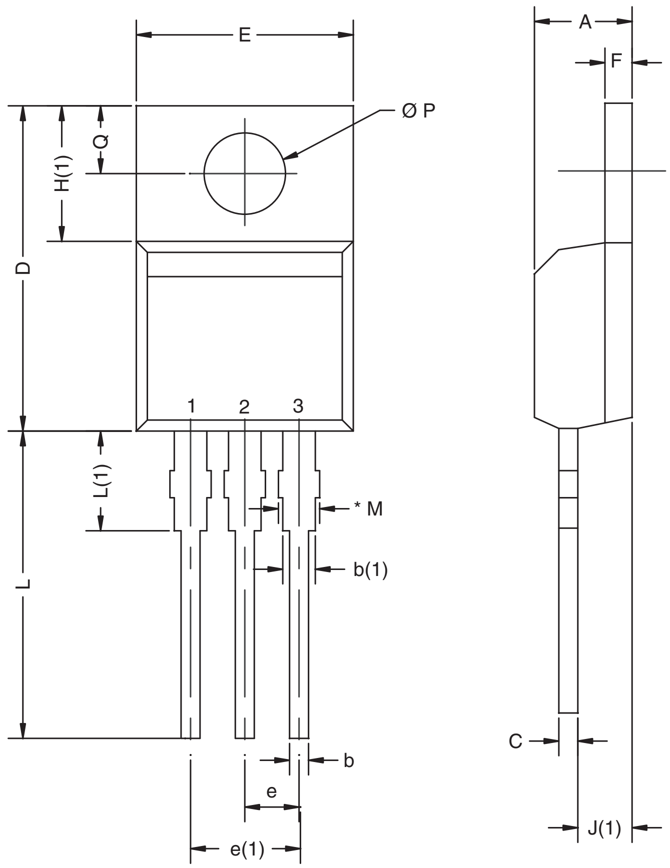
TO-220AB



DIM.	MILLIMETERS MIN.	MILLIMETERS MAX.	INCHES MIN.	INCHES MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X10-0416-Rev. M, 01-Nov-10 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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